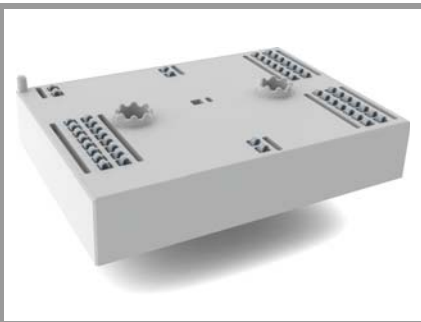


SKiiP39GAL17E4V1



MiniSKiiP® 3

Boost Chopper

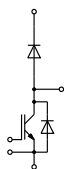
SKiiP39GAL17E4V1

Features*

- Trench IGBTs
- Robust and soft switching freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532
- NTC T-Sensor

Remarks

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GAL

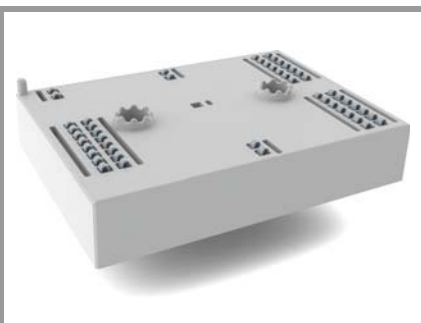
Absolute Maximum Ratings			
Symbol	Conditions	Values	Unit
IGBT 1			
V_{CES}	$T_j = 25^\circ\text{C}$	1700	V
I_C	$\lambda_{paste}=0.8 \text{ W/(mK)}$	$T_s = 25^\circ\text{C}$	307
	$T_j = 175^\circ\text{C}$	$T_s = 70^\circ\text{C}$	249
I_C	$\lambda_{paste}=2.5 \text{ W/(mK)}$	$T_s = 25^\circ\text{C}$	371
	$T_j = 175^\circ\text{C}$	$T_s = 70^\circ\text{C}$	301
I_{Chom}		300	A
I_{CRM}		900	A
V_{GES}		-20 ... 20	V
t_{psc}	$V_{CC} = 1000 \text{ V}$ $V_{GE} \leq 15 \text{ V}$ $V_{CES} \leq 1700 \text{ V}$	$T_j = 150^\circ\text{C}$	10
T_j		-40 ... 175	$^\circ\text{C}$

Absolute Maximum Ratings			
Symbol	Conditions	Values	Unit
Diode 1			
V_{RRM}	$T_j = 25^\circ\text{C}$	1700	V
I_F	$\lambda_{paste}=0.8 \text{ W/(mK)}$	$T_s = 25^\circ\text{C}$	283
	$T_j = 175^\circ\text{C}$	$T_s = 70^\circ\text{C}$	222
I_F	$\lambda_{paste}=2.5 \text{ W/(mK)}$	$T_s = 25^\circ\text{C}$	335
	$T_j = 175^\circ\text{C}$	$T_s = 70^\circ\text{C}$	265
I_{FRM}		600	A
I_{FSM}	10 ms	$T_j = 25^\circ\text{C}$	1755
	sin 180°	$T_j = 150^\circ\text{C}$	1566
T_j		-40 ... 175	$^\circ\text{C}$

Absolute Maximum Ratings			
Symbol	Conditions	Values	Unit
Diode 2			
V_{RRM}	$T_j = 25^\circ\text{C}$	1700	V
I_F	$\lambda_{paste}=0.8 \text{ W/(mK)}$	$T_s = 25^\circ\text{C}$	52
	$T_j = 175^\circ\text{C}$	$T_s = 70^\circ\text{C}$	42
I_F	$\lambda_{paste}=2.5 \text{ W/(mK)}$	$T_s = 25^\circ\text{C}$	59
	$T_j = 175^\circ\text{C}$	$T_s = 70^\circ\text{C}$	47
I_{FRM}		80	A
I_{FSM}	10 ms	$T_j = 25^\circ\text{C}$	280
	sin 180°	$T_j = 150^\circ\text{C}$	280
T_j		-40 ... 175	$^\circ\text{C}$

Absolute Maximum Ratings			
Symbol	Conditions	Values	Unit
Module			
$I_{t(RMS)}$	20 A per spring	280	A
T_{stg}	module without TIM	-40 ... 125	$^\circ\text{C}$
V_{isol}	AC sinus 50 Hz, t = 1 min	2500	V

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Features*

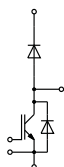
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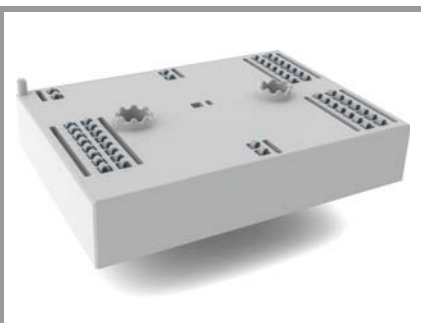
Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
IGBT 1						
$V_{CE(sat)}$	$I_C = 300\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$		1.90	2.20	V
		$T_j = 150^\circ\text{C}$		2.30	2.60	V
V_{CE0}	chipelevel	$T_j = 25^\circ\text{C}$		0.80	0.90	V
		$T_j = 150^\circ\text{C}$		0.70	0.80	V
r_{CE}	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$		3.7	4.3	m Ω
		$T_j = 150^\circ\text{C}$		5.3	6.0	m Ω
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 12\text{ mA}$		5.2	5.8	6.4	V
I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = 1700\text{ V}, T_j = 25^\circ\text{C}$				0.3	mA
C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$		27.20		nF
C_{oes}		$f = 1\text{ MHz}$		1.06		nF
C_{res}		$f = 1\text{ MHz}$		0.88		nF
Q_G	$V_{GE} = -8\text{ V} \dots +15\text{ V}$			2400		nC
R_{Gint}	$T_j = 25^\circ\text{C}$			2.1		Ω
$t_{d(on)}$	$V_{CC} = 900\text{ V}$	$I_C = 300\text{ A}$ $V_{GE} = +15/-15\text{ V}$		216		ns
t_r	$R_{G on} = 2\ \Omega$			52		ns
E_{on}	$R_{G off} = 2\ \Omega$			47		mJ
$t_{d(off)}$	$di/dt_{on} = 7900\text{ A}/\mu\text{s}$			697		ns
t_f	$di/dt_{off} = 2025\text{ A}/\mu\text{s}$			167		ns
E_{off}	$dv/dt = 5084\text{ V}/\mu\text{s}$ $L_s = 25\text{ nH}$			102		mJ
$R_{th(j-s)}$	per IGBT, $\lambda_{paste}=0.8\text{ W}/(\text{mK})$			0.18		K/W
$R_{th(j-s)}$	per IGBT, $\lambda_{paste}=2.5\text{ W}/(\text{mK})$			0.13		K/W

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Diode 1						
V_F	$I_F = 300\text{ A}$ $V_{GE} = 0\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$		2.00	2.40	V
		$T_j = 150^\circ\text{C}$		2.15	2.57	V
V_{F0}	chipelevel	$T_j = 25^\circ\text{C}$		1.32	1.56	V
		$T_j = 150^\circ\text{C}$		1.08	1.22	V
r_F	chipelevel	$T_j = 25^\circ\text{C}$		2.3	2.8	m Ω
		$T_j = 150^\circ\text{C}$		3.6	4.5	m Ω
I_{RRM}	$I_F = 300\text{ A}$			517		A
Q_{rr}	$di/dt_{off} = 8569\text{ A}/\mu\text{s}$			100		μC
E_{rr}	$V_{GE} = -15\text{ V}$ $V_{CC} = 1200\text{ V}$			69		mJ
$R_{th(j-s)}$	per Diode, $\lambda_{paste}=0.8\text{ W}/(\text{mK})$			0.22		K/W
$R_{th(j-s)}$	per Diode, $\lambda_{paste}=2.5\text{ W}/(\text{mK})$			0.17		K/W



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MiniSKiiP® 3

Boost Chopper

SKiiP39GAL17E4V1

Features*

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- Highly reliable spring contacts for electrical connections
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- NTC T-Sensor

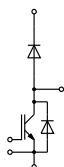
Remarks

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- IGBT 1 = T2

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Diode 2						
V_F	$I_F = 40\text{ A}$ $V_{GE} = 0\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$		2.00	2.38	V
		$T_j = 150^\circ\text{C}$		2.14	2.56	V
V_{F0}	chipelevel	$T_j = 25^\circ\text{C}$		1.32	1.56	V
		$T_j = 150^\circ\text{C}$		1.08	1.22	V
r_F	chipelevel	$T_j = 25^\circ\text{C}$		17	20	m Ω
		$T_j = 150^\circ\text{C}$		27	33	m Ω
I_{RRM}	$I_F = 40\text{ A}$			t.b.d.		A
Q_{rr}	$V_{GE} = -15\text{ V}$ $V_{CC} = 1200\text{ V}$			t.b.d.		μC
E_{rr}				t.b.d.		mJ
$R_{th(j-s)}$	per Diode, $\lambda_{paste}=0.8\text{ W/(mK)}$			1		K/W
$R_{th(j-s)}$	per Diode, $\lambda_{paste}=2.5\text{ W/(mK)}$			0.83		K/W

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Module						
M_s	to heat sink		2		2.5	Nm
w	weight			82		g

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Temperature Sensor						
R_{100}	$T_c=100^\circ\text{C}$ ($R_{25}=5\text{ k}\Omega$)			$493 \pm 5\%$		Ω
$B_{25/85}$	$R_{(T)}=R_{25} \cdot \exp[B_{25/85} \cdot (1/T-1/298)]$, T[K]			3420		K



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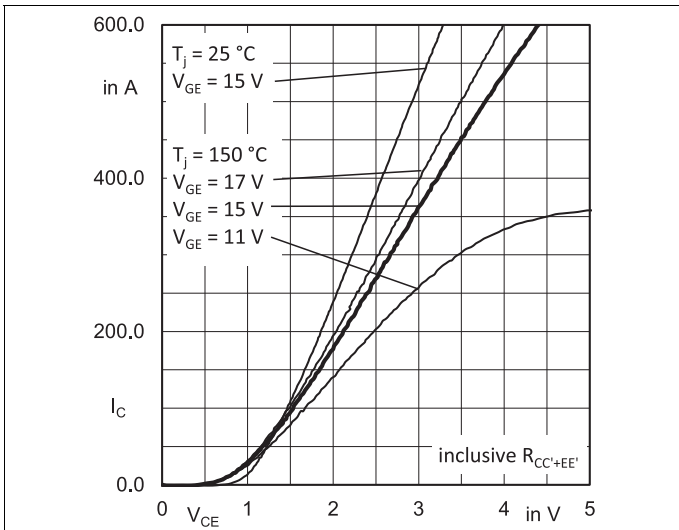


Fig. 1: Typ. output characteristic

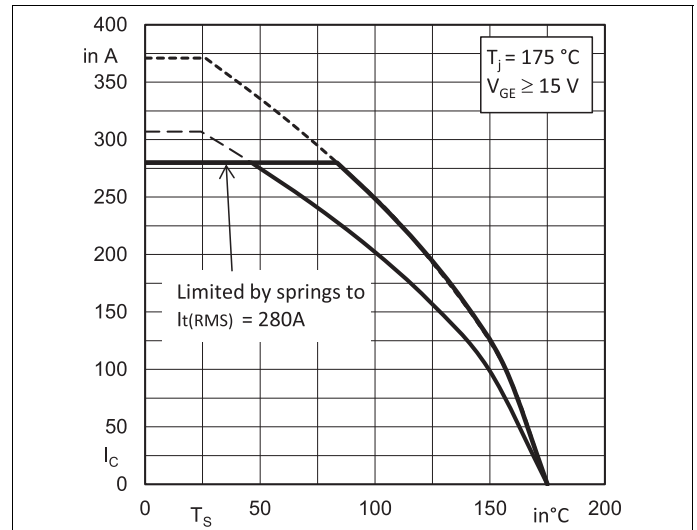


Fig. 2: Rated current vs. temperature $I_C = f(T_S)$

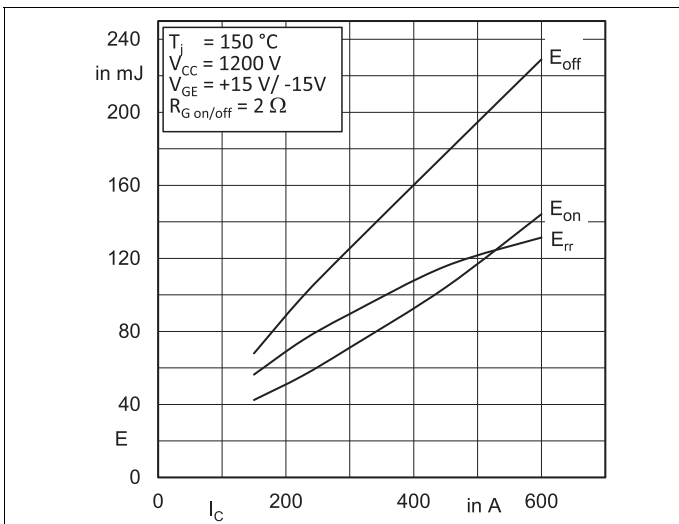


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

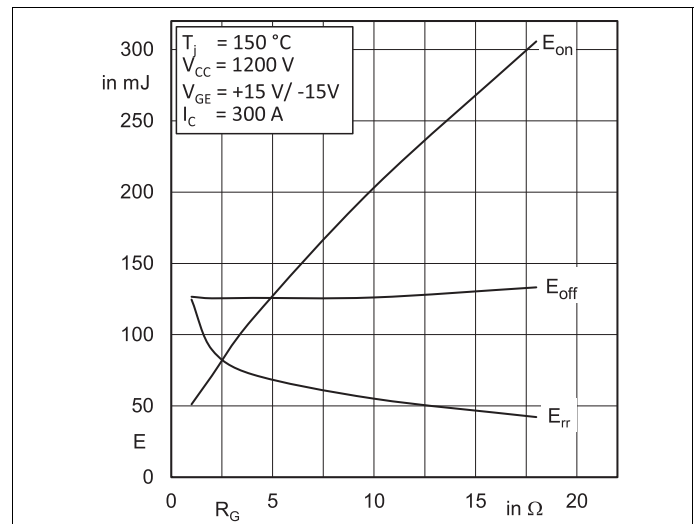


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

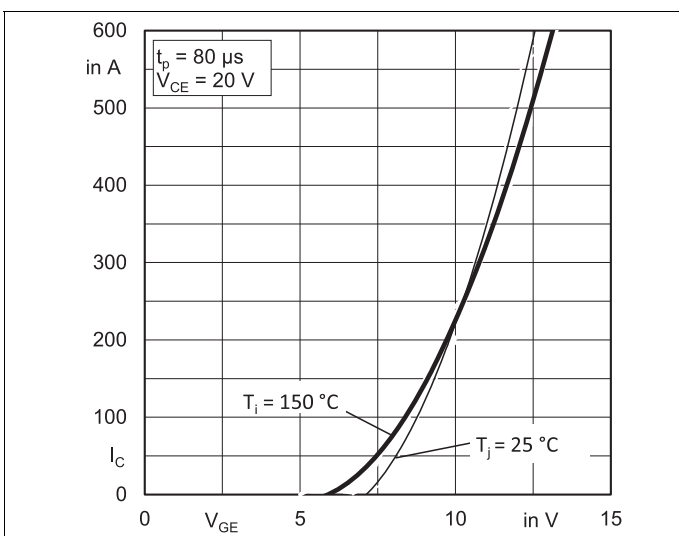


Fig. 5: Typ. transfer characteristic

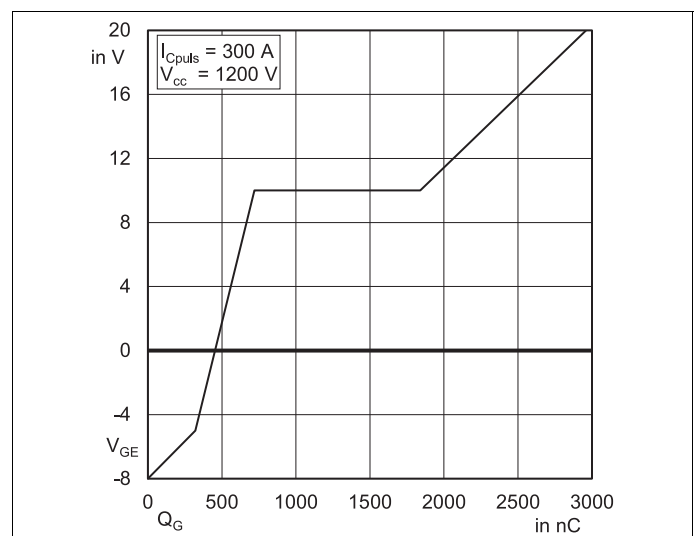


Fig. 6: Typ. gate charge characteristic

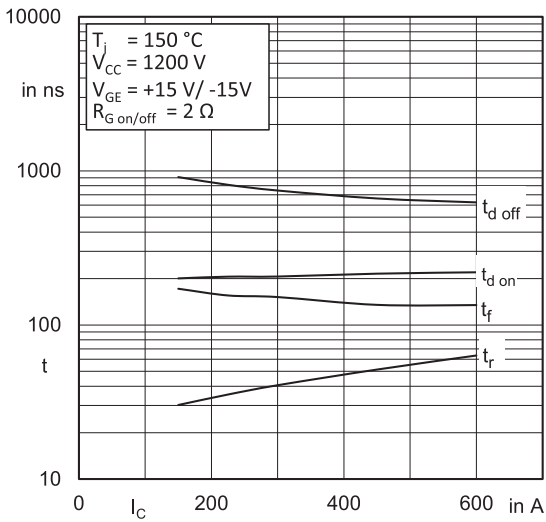


Fig. 7: Typ. switching times vs. I_C

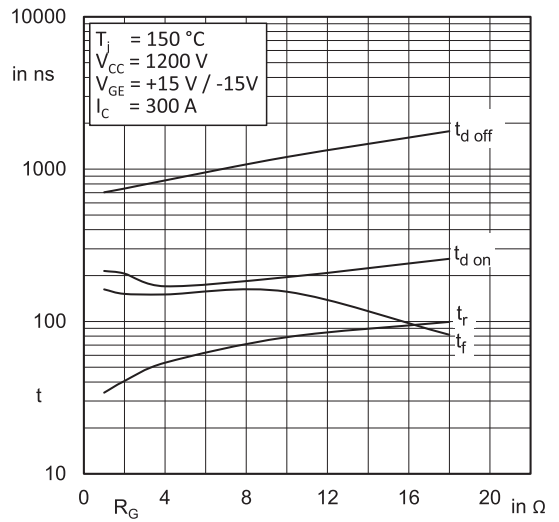


Fig. 8: Typ. switching times vs. gate resistor R_G

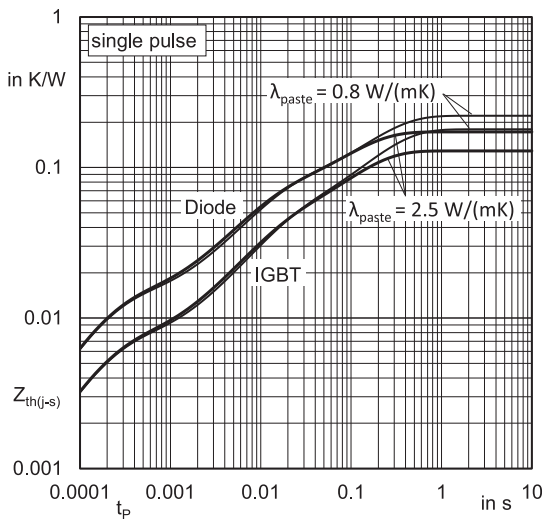


Fig. 9: Typ. transient thermal impedance

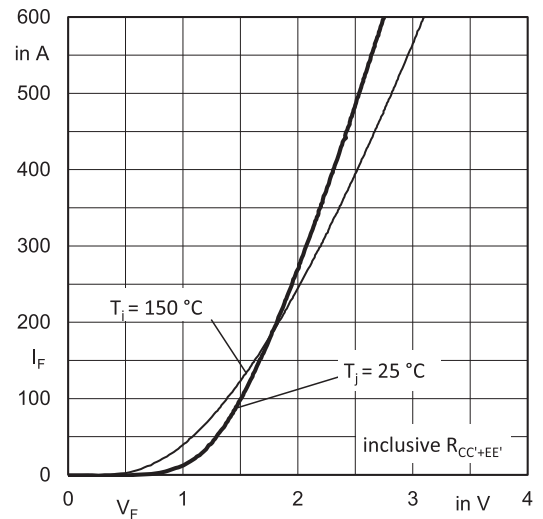


Fig. 10: Typ. CAL diode forward characteristic

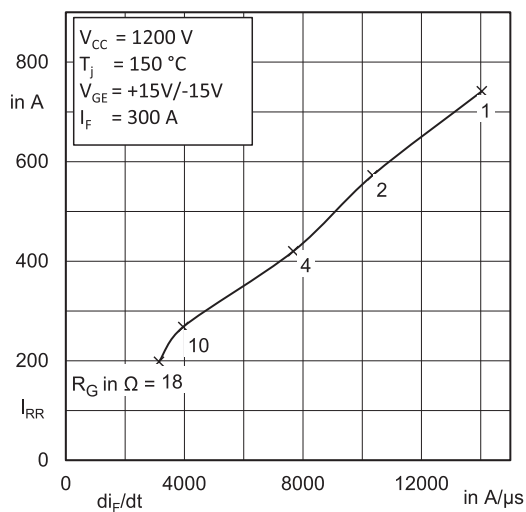


Fig. 11: Typ. CAL diode peak reverse recovery current

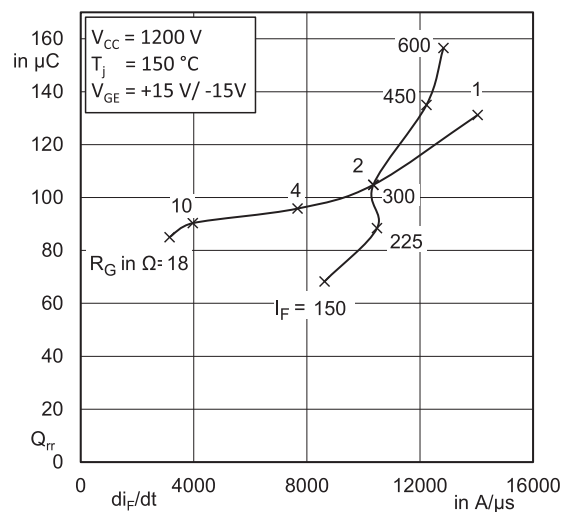
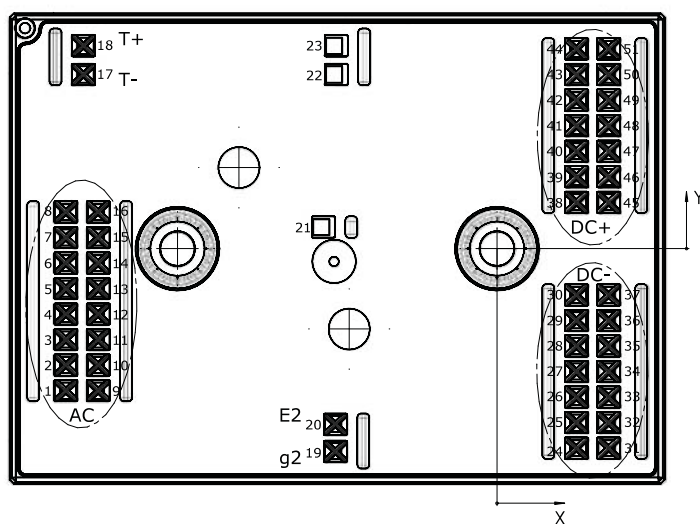


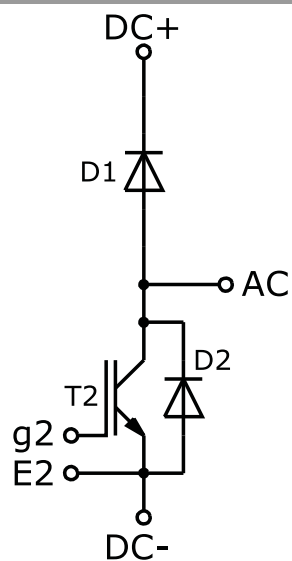
Fig. 12: Typ. CAL diode recovery charge

Pin out											
Pin	X	Y	Function	Pin	X	Y	Function	Pin	X	Y	Function
1	-53,98	-17,80	AC	18	-51,78	25,40	T+	35	13,98	-12,20	DC-
2	-53,98	-14,60	AC	19	-20,23	-25,40	g2	36	13,98	-9,00	DC-
3	-53,98	-11,40	AC	20	-20,23	-22,00	E2	37	13,98	-5,80	DC-
4	-53,98	-8,20	AC	21	-21,73	2,70		38	9,93	5,80	DC+
5	-53,98	-5,00	AC	22	-20,13	21,80		39	9,93	9,00	DC+
6	-53,98	-1,80	AC	23	-20,13	25,40		40	9,93	12,20	DC+
7	-53,98	1,40	AC	24	9,93	-25,00	DC-	41	9,93	15,40	DC+
8	-53,98	4,60	AC	25	9,93	-21,80	DC-	42	9,93	18,60	DC+
9	-49,93	-17,80	AC	26	9,93	-18,60	DC-	43	9,93	21,80	DC+
10	-49,93	-14,60	AC	27	9,93	-15,40	DC-	44	9,93	25,00	DC+
11	-49,93	-11,40	AC	28	9,93	-12,20	DC-	45	13,98	5,80	DC+
12	-49,93	-8,20	AC	29	9,93	-9,00	DC-	46	13,98	9,00	DC+
13	-49,93	-5,00	AC	30	9,93	-5,80	DC-	47	13,98	12,20	DC+
14	-49,93	-1,80	AC	31	13,98	-25,00	DC-	48	13,98	15,40	DC+
15	-49,93	1,40	AC	32	13,98	-21,80	DC-	49	13,98	18,60	DC+
16	-49,93	4,60	AC	33	13,98	-18,60	DC-	50	13,98	21,80	DC+
17	-51,78	21,80	T-	34	13,98	-15,40	DC-	51	13,98	25,00	DC+

all values in [mm]



Pinout and Dimensions



Pinout

This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

***IMPORTANT INFORMATION AND WARNINGS**

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